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L8: Entry 1 of 16

File: JPAB

Feb 2, 2000

PUB-NO: JP02000036572A

DOCUMENT-IDENTIFIER: JP 2000036572 A

TITLE: MANUFACTURE OF EMBEDDED DYNAMIC RANDOM ACCESS MEMORY

PUBN-DATE: February 2, 2000

## INVENTOR-INFORMATION:

NAME

COUNTRY

LIOU, FU-TAI

RO, KATETSU

## ASSIGNEE-INFORMATION:

NAME

COUNTRY

UNITED MICROELECTRONICS CORP

APPL-NO: JP10304330

APPL-DATE: October 26, 1998

PRIORITY-DATA: 1998TW-110879 (July 6, 1998)

INT-CL (IPC): H01 L 27/108; H01 L 21/8242

## ABSTRACT:

PROBLEM TO BE SOLVED: To improve the flatness of an integrated circuit by hydrogen-treating a heat resistant metal oxide deposited by using a hydrogen plasma or hot hydrogen, and altering non-electric conductivity of the treated metal oxide to electric conductivity.

SOLUTION: A heat resistant metal oxide layer hydrogen-treated by using a hydrogen plasma or hot hydrogen and exposed is converted into a conductive layer. Heat resistant metal oxide layers 116b1 116b2 exposed by the hydrogen-treatment are converted into conductive layers. Meanwhile, non-exposed heat resistant metal oxide layer 116a is still retained in a state of a non-conductive layer. A second conductive layer is formed on the metal oxide layer, and then patterned. As a result an upper surface of an upper electrode 118a of a capacitor 120 and first and second contact mutual connectors 121, 122 become the same relative heights. Thus, the smoothness (flatness) of the integrated circuit can be improved.

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L5: Entry 1 of 1

File: JPAB

Aug 7, 2001

PUB-NO: JP02001213696A

DOCUMENT-IDENTIFIER: JP 2001213696 A

TITLE: MANUFACTURING METHOD OF EPITAXIAL WAFER AND ITS SEMICONDUCTOR MANUFACTURING EQUIPMENT

PUBN-DATE: August 7, 2001

## INVENTOR-INFORMATION:

NAME

COUNTRY

OTA, YUTAKA

TANAKA, NORIMICHI

## ASSIGNEE-INFORMATION:

NAME

COUNTRY

SHIN ETSU HANDOTAI CO LTD

APPL-NO: JP2000127495

APPL-DATE: April 27, 2000

PRIORITY-DATA: 1999JP-2061 (November 22, 1999)

INT-CL (IPC): C30 B 29/06; H01 L 21/205; H01 L 21/31

## ABSTRACT:

PROBLEM TO BE SOLVED: To prevent putting on an epitaxial layer caused during cleaning by controlling metal fine particle not attached directly to the layer.

SOLUTION: The epitaxial wafer EPW obtained at the step S2 is taken out from the reaction chamber at the step S3 and then immediately contacted with the air containing ozone at the S4 to form the chemical silicon oxidation membrane on the surface of the epitaxial layer E. Even when the metal fine particle is attached during a certain measurement and inspection at the step 5 and the step 6, the chemical silicon oxidation membrane controls oxidation- reduction reaction between the silicon epitaxial layer E and the metal fine particle M, leading not to the strong attachment of the particle. Thanks to this, pit is not caused at the silicon epitaxial layer E even after SC1 cleaning and SC2 cleaning at the step S7.

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L4: Entry 1 of 3

File: JPAB

Jun 12, 1990

PUB-NO: JP402153082A

DOCUMENT-IDENTIFIER: JP 02153082 A

TITLE: RETREATMENT OF WASTE PIRANHA ACID AND APPARATUS THEREFOR

PUBN-DATE: June 12, 1990

## INVENTOR-INFORMATION:

NAME

COUNTRY

DOBSON, JESSE C

MCCORMICK, MARSHALL

## ASSIGNEE-INFORMATION:

NAME

COUNTRY

ALAMEDA INSTR INC

APPL-NO: JP01207030

APPL-DATE: August 11, 1989

INT-CL (IPC): C23F 1/46

## ABSTRACT:

PURPOSE: To obtain high-purity products and to lessen the consumption of an apparatus by stabilizing the temp. of waste piranha acid in a charging section, then lowering a pressure in a distillation system to refine sulfuric acid and transferring the waste to a removing system.

CONSTITUTION: The piranha acid used in washing, etching, etc., of semiconductors is introduced from a charging line 1 into a prepn. device (charging section) 2 where the temp. is stabilized. The piranha acid is then discharged gradually to the product distillation system 3. The pressure is lowered and the temp. is elevated in the treatment process. The refined sulfuric acid (product) is transferred into an accepting tank 8 or is recirculated to a junction point 11. The waste acid, heavy metal contaminant and particulates (sludge) are transferred from the product distillation system 3 to a waste removing system 4 and are discharged to a waste collecting tank 9. A coolant system 5 is used for changing the temp. of the coolant of the cooler of the distillation system 3. Feed water cools the heat exchanger of the waste removing system 4.

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L2: Entry 5 of 5

File: DWPI

Feb 23, 1979

DERWENT-ACC-NO: 1979-24942B

DERWENT-WEEK: 197913

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TITLE: Etching cobalt-nickel alloy film for electrical applications - using aq. hydrochloric acid contg. hydrogen peroxide

PATENT-ASSIGNEE: SHARP KK (SHAF)

PRIORITY-DATA: 1977JP-0089554 (July 25, 1977)

[Search Selected](#)[Search ALL](#)[Clear](#)

## PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
<input type="checkbox"/> <u>JP 54024236 A</u>	February 23, 1979		000	

INT-CL (IPC): C23C 1/02; H01L 21/30

ABSTRACTED-PUB-NO: JP 54024236A

## BASIC-ABSTRACT:

Fine working of a Co-Ni alloy film is by using an etching liq. of aq. hydrochloric acid soln. contg. hydrocarbon peroxide as oxidising agent in contact with metal surface to etch an electrical pattern.

ABSTRACTED-PUB-NO: JP 54024236A

## EQUIVALENT-ABSTRACTS:

DERWENT-CLASS: L03 M14 U11 U12

CPI-CODES: L03-A01; M14-A;